TEMIC
Semiconductors

DG183/184/185

High-Speed Drivers with Dual DPST JFET Switches

Features

- Constant On-Resistance Over Entire Analog Range
- Low Leakage
- Low Crosstalk
- Break-Before-Make Switching
- Rad Hardness

Benefits

- Low Distortion
- Eliminates Large Signal Errors
- High Precision
- Improved Channel Isolation
- Eliminates Inadvertent Shorting Between Channels
- Fault Protection

Applications

- Audio Switching
- Precision Switching
- Video Switching
- Video Routing
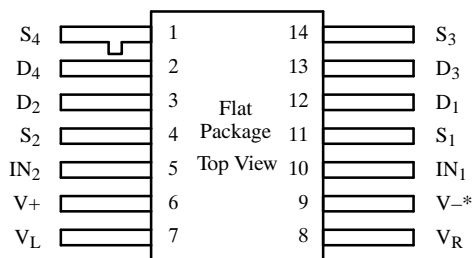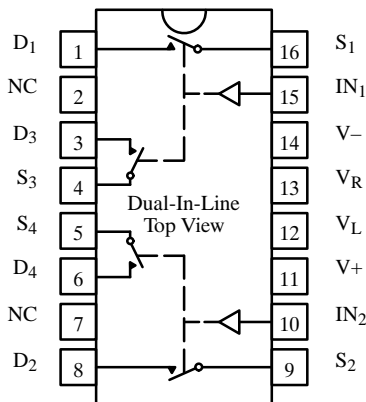- Sample/Hold
- Aerospace

Description

The DG183/184/185 are precision dual double-pole, single-throw (DPST) analog switches designed to provide accurate switching of video and audio signals. This series is ideally suited for applications requiring a constant on-resistance over the entire analog range.

The major difference in the devices is the on-resistance (DG183—10 Ω, DG184—30 Ω, DG185—75 Ω). Reduced errors are achieved through low leakage current ($I_{D(on)}$ < 2 nA). Applications which benefit from the flat JFET on-resistance include audio switching, video switching, and data acquisition.

To achieve fast and accurate switch performance, each device comprises four n-channel JFET transistors and a TTL compatible bipolar driver. In the on state, each switch conducts current equally well in either direction. In the off condition, the switches will block up to 20 V peak-to-peak, with feedthrough of less than –60 dB at 10 MHz.

Functional Block Diagram and Pin Configuration

Dual-In-Line Top View

Flat Package Top View

Refer to JAN38510 Information, Military Section
*Common to Substrate and Case

Truth Table

Logic	Switch
0	OFF
1	ON

Logic "0" ≤ 0.8 V
Logic "1" ≥ 2.0 V

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70032.

Ordering Information

Temp Range	Package	Part Number
−25 to 85°C	16-Pin Sidebraze	DG183BP
		DG184BP
−55 to 125°C	16-Pin Sidebraze	DG183AP/883
		DG184AP/883, JM38510/11103BEA
		DG185AP/883, JM38510/11104BEA
	14-Pin Flat Pack	JM38510/11103BXA
		JM38510/11104BXA

Absolute Maximum Ratings

V+ to V– . . . . 36 V

V+ to V_D . . . . 33 V

V_D to V– . . . . 33 V

V_D to V_D . . . . ±22 V

V_L to V– . . . . 36 V

V_L to V_{IN} . . . . 8 V

V_L to V_R . . . . 8 V

V_{IN} to V_R . . . . 8 V

V_R to V– . . . . 27 V

V_R to V_{IN} . . . . 2 V

Current (S or D) DG183 . . . . 200 mA

Current (S or D) DG184, DG185 . . . . 30 mA

Current (All Other Pins) . . . . 30 mA

Storage Temperature . . . . −65 to 150°C

Power Dissipation[a]

16-Pin Sidebraze[b] . . . . 900 mW

14-Pin Flat Pack[c] . . . . 900 mW

Notes:
a.   All leads welded or soldered to PC Board.
b.   Derate 12 mW/°C above 75°C
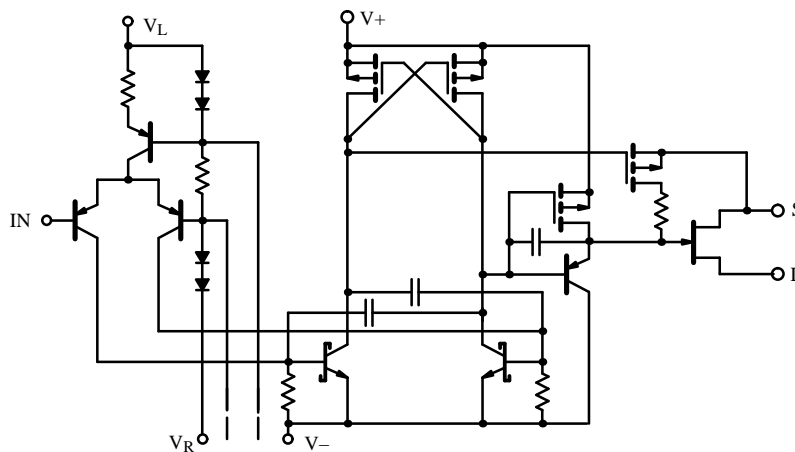c.   Derate 10 mW/°C above 75°C

Schematic Diagram (Typical Channel)

Figure 1.

Specifications[a] for DG183

Parameter	Symbol	Test Conditions Unless Otherwise Specified $V+ = 15$ V, $V- = -15$ V, $V_L = 5$ V $V_R = 0$ V, $V_{IN} = 0.8$ V or 2 V[f]	Temp[b]	Typ[c]	A Suffix −55 to 125°C Min[d]	A Suffix −55 to 125°C Max[d]	B Suffix −25 to 85°C Min[d]	B Suffix −25 to 85°C Max[d]	Unit
Analog Switch									
Analog Signal Range[e]	V_{ANALOG}		Full		−7.5	15	−7.5	15	V
Drain-Source On-Resistance	$r_{DS(on)}$	$I_S = -10$ mA, $V_D = -7.5$ V	Room Full	7.5		10 20		15 25	Ω
Source Off Leakage Current	$I_{S(off)}$	$V_S = \pm 10$ V, $V_D = \mp 10$ V $V+ = 10$ V, $V- = -20$ V	Room Hot	0.05		10 1000		15 300	nA
Source Off Leakage Current	$I_{S(off)}$	$V_S = \pm 7.5$ V, $V_D = \mp 7.5$ V	Room Hot	0.05		10 1000		15 300	nA
Drain Off Leakage Current	$I_{D(off)}$	$V_S = \pm 10$ V, $V_D = \mp 10$ V $V+ = 10$ V, $V- = -20$ V	Room Hot	0.04		10 1000		15 300	nA
Drain Off Leakage Current	$I_{D(off)}$	$V_S = \pm 7.5$ V, $V_D = \mp 7.5$ V	Room Hot	0.03		10 1000		15 300	nA
Channel On Leakage Current	$I_{D(on)}$	$V_D = V_S = \pm 7.5$ V	Room Hot	−0.1	−2 −200		−10 −200		nA
Saturation Drain Current	I_{DSS}	2 ms Pulse Duration	Room	300					mA
Digital Input									
Input Current with Input Voltage High	I_{INH}	$V_{IN} = 5$ V	Room Hot	<0.01		10 20		10 20	μA
Input Current with Input Voltage Low	I_{INL}	$V_{IN} = 0$ V	Full	−30	−250		−250		μA
Dynamic Characteristics									
Turn-On Time	t_{on}	See Switching Time Test Circuit	Room	240		400		600	ns
Turn-Off Time	t_{off}	See Switching Time Test Circuit	Room	140		200		220	ns
Source-Off Capacitance	$C_{S(off)}$	$f = 1$ MHz, $V_S = -5$ V, $I_D = 0$	Room	21					pF
Drain-Off Capacitance	$C_{D(off)}$	$f = 1$ MHz, $V_D = -5$ V, $I_S = 0$	Room	17					pF
Channel-On Capacitance	$C_{D(on)}$	$V_D = V_S = 0$ V	Room	17					pF
Off Isolation	OIRR	$f = 1$ MHz, $R_L = 75$ Ω	Room	>55					dB
Power Supplies									
Positive Supply Current	I+	$V_{IN} = 0$ V, or 5 V	Room	0.6		1.5		1.5	mA
Negative Supply Current	I−	$V_{IN} = 0$ V, or 5 V	Room	−2.7	−5		−5		mA
Logic Supply Current	I_L	$V_{IN} = 0$ V, or 5 V	Room	3.1		4.5		4.5	mA
Reference Supply Current	I_R	$V_{IN} = 0$ V, or 5 V	Room	−1	−2		−2		mA

Notes:
a. Refer to PROCESS OPTION FLOWCHART .
b. Room = 25°C, Full = as determined by the operating temperature suffix.
c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
e. Guaranteed by design, not subject to production test.
f. V_{IN} = input voltage to perform proper function.

Specifications[a] for DG184

Parameter	Symbol	Test Conditions Unless Otherwise Specified $V+ = 15\ V, V- = -15\ V, V_L = 5\ V$ $V_R = 0\ V, V_{IN} = 0.8\ V$ or $2\ V^f$	Temp[b]	Typ[c]	A Suffix −55 to 125°C Min[d]	Max[d]	B Suffix −25 to 85°C Min[d]	Max[d]	Unit
Analog Switch									
Analog Signal Range[e]	V_{ANALOG}		Full		−7.5	15	−7.5	15	V
Drain-Source On-Resistance	$r_{DS(on)}$	$I_S = -10\ mA, V_D = -7.5\ V$	Room Full	22		30 60		50 75	Ω
Source Off Leakage Current	$I_{S(off)}$	$V_S = \pm 10\ V, V_D = \mp 10\ V$ $V+ = 10\ V, V- = -20\ V$	Room Hot	0.06		1 100		5 100	nA
		$V_S = \pm 7.5\ V, V_D = \mp 7.5\ V$	Room Hot	0.05		1 100		5 100	
Drain Off Leakage Current	$I_{D(off)}$	$V_S = \pm 10\ V, V_D = \mp 10\ V$ $V+ = 10\ V, V- = -20\ V$	Room Hot	0.4		1 100		5 100	nA
		$V_S = \pm 7.5\ V, V_D = \mp 7.5\ V$	Room Hot	0.3		1 100		5 100	
Channel On Leakage Current	$I_{D(on)}$	$V_D = V_S = \pm 7.5\ V$	Room Hot	−0.02	−2 −200		−10 −200		nA
Digital Input									
Input Current with Input Voltage High	I_{INH}	$V_{IN} = 5\ V$	Room Hot	<0.01		10 20		10 20	μA
Input Current with Input Voltage Low	I_{INL}	$V_{IN} = 0\ V$	Full	−30	−250		−250		μA
Dynamic Characteristics									
Turn-On Time	t_{on}	See Switching Time Test Circuit	Room	85		150		180	ns
Turn-Off Time	t_{off}		Room	95		130		150	ns
Source-Off Capacitance	$C_{S(off)}$	$V_S = -5\ V, I_D = 0$	Room	9					pF
Drain-Off Capacitance	$C_{D(off)}$	$f = 1\ MHz$ $V_D = -5\ V, I_S = 0$	Room	6					pF
Channel-On Capacitance	$C_{D(on)}$	$V_D = V_S = 0\ V$	Room	14					
Off Isolation	OIRR	$f = 1\ MHz, R_L = 75\ Ω$	Room	>50					dB
Power Supplies									
Positive Supply Current	I+		Room	0.6		3		3	mA
Negative Supply Current	I−	$V_{IN} = 0\ V,$ or $5\ V$	Room	−2.7	−5.5		−5.5		mA
Logic Supply Current	I_L		Room	3.1		4.5		4.5	
Reference Supply Current	I_R		Room	−1	−2		−2		

Notes:
a. Refer to PROCESS OPTION FLOWCHART .
b. Room = 25°C, Full = as determined by the operating temperature suffix.
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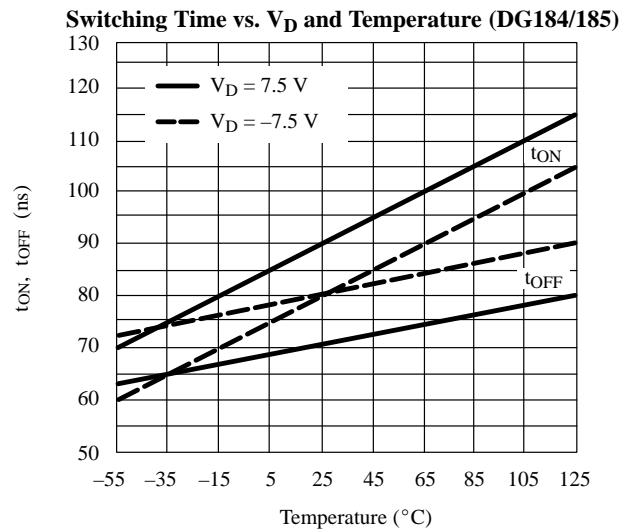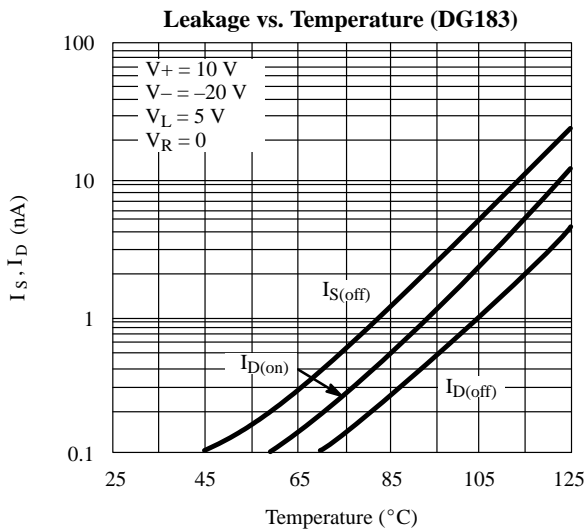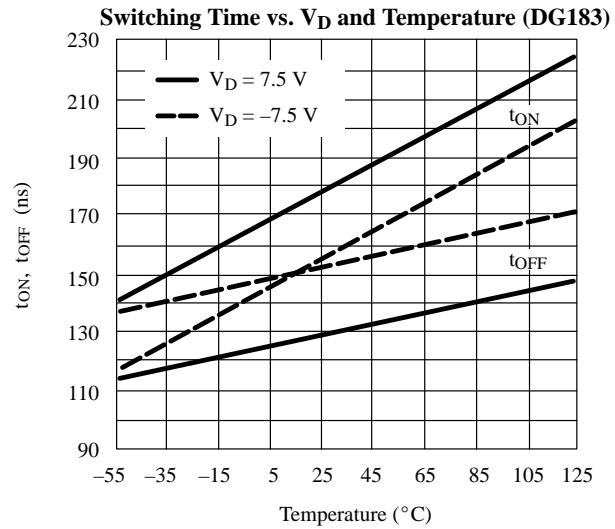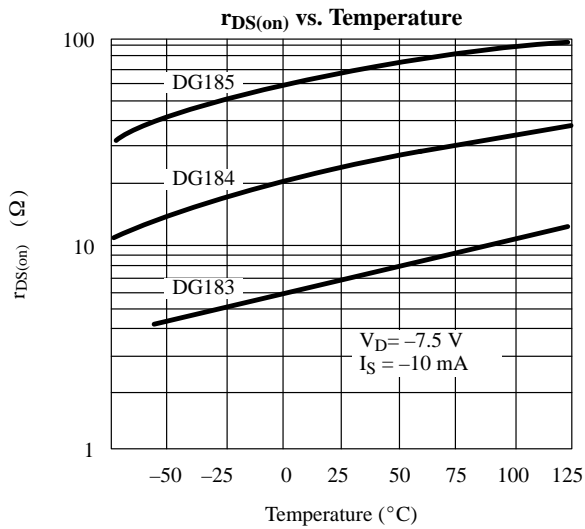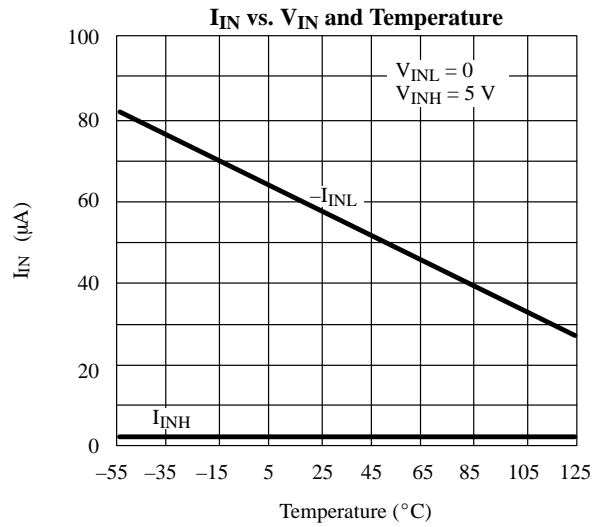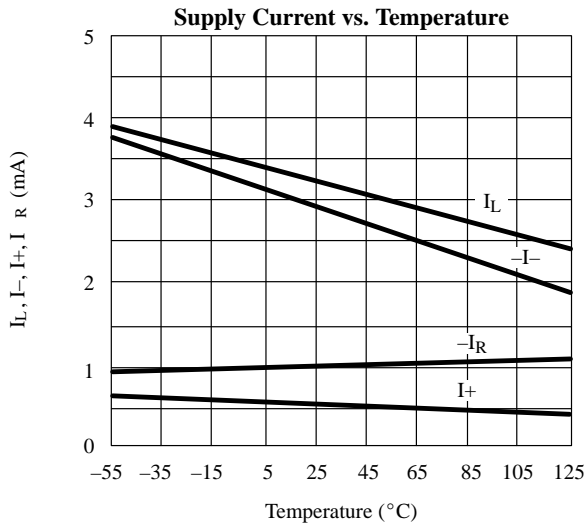f. V_{IN} = input voltage to perform proper function.

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Specifications[a] for DG185

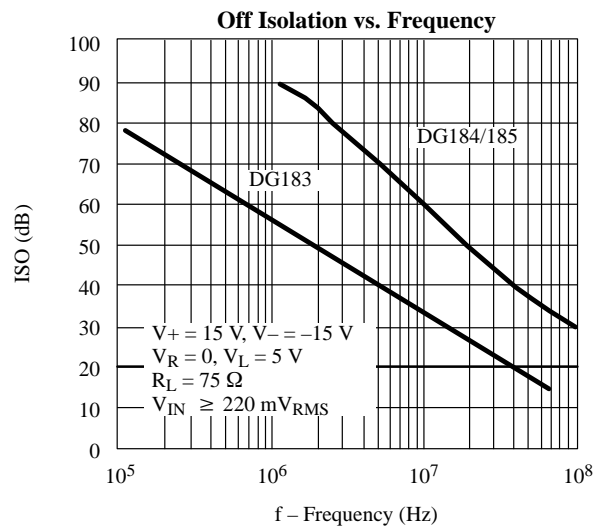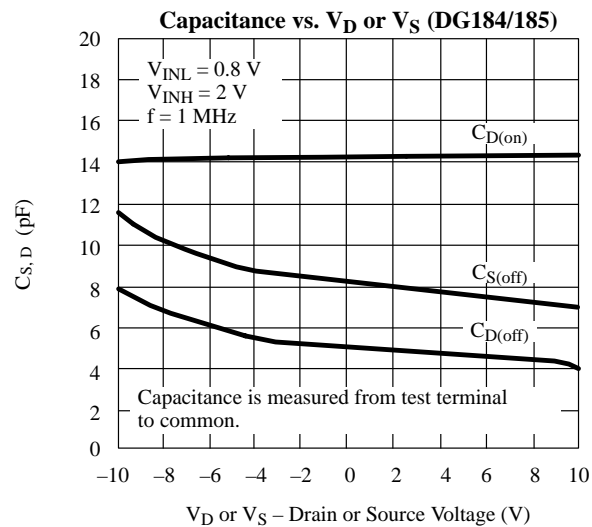| Parameter	Symbol	Test Conditions Unless Otherwise Specified V+ = 15 V, V− = −15 V, V$_L$ = 5 V V$_R$ = 0 V, V$_{IN}$ = 0.8 V or 2 V[f]	Temp[b]	Typ[c]	A Suffix −55 to 125°C Min[d]	Max[d]	B Suffix −25 to 85°C Min[d]	Max[d]	Unit
Analog Switch									
Analog Signal Range[e]	V$_{ANALOG}$		Full		−10	15	−10	15	V
Drain-Source On-Resistance	r$_{DS(on)}$	I$_S$ = −10 mA, V$_D$ = −7.5 V	Room Full	35		75 150		100 150	Ω
Source Off Leakage Current	I$_{S(off)}$	V$_S$ = ± 10 V, V$_D$ = ∓ 10 V V+ = 10 V, V− = −20 V	Room Hot	0.05		1 100		5 100	nA
		V$_S$ = ± 10 V, V$_D$ = ∓ 10 V	Room Hot	0.07		1 100		5 100	
Drain Off Leakage Current	I$_{D(off)}$	V$_S$ = ± 10 V, V$_D$ = ∓ 10 V V+ = 10 V, V− = −20 V	Room Hot	0.4		1 100		5 100	nA
		V$_S$ = ± 10 V, V$_D$ = ∓ 10 V	Room Hot	0.3		1 100		5 100	
Channel On Leakage Current	I$_{D(on)}$	V$_D$ = V$_S$ = ± 10 V	Room Hot	−0.03	−2 −200		−10 −200		nA
Digital Input									
Input Current with Input Voltage High	I$_{INH}$	V$_{IN}$ = 5 V	Room Hot	<0.01		10 20		10 20	μA
Input Current with Input Voltage Low	I$_{INL}$	V$_{IN}$ = 0 V	Full	−30	−250		−250		μA
Dynamic Characteristics									
Turn-On Time	t$_{on}$	See Switching Time Test Circuit	Room	120		250		300	ns
Turn-Off Time	t$_{off}$		Room	100		130		150	ns
Source-Off Capacitance	C$_{S(off)}$	f = 1 MHz / V$_S$ = −5 V, I$_D$ = 0	Room	9					pF
Drain-Off Capacitance	C$_{D(off)}$	f = 1 MHz / V$_D$ = −5 V, I$_S$ = 0	Room	6					pF
Channel-On Capacitance	C$_{D(on)}$	V$_D$ = V$_S$ = 0 V	Room	14					pF
Off Isolation	OIRR	f = 1 MHz, R$_L$ = 75 Ω	Room	>50					dB
Power Supplies									
Positive Supply Current	I+		Room	0.6		3		3	mA
Negative Supply Current	I−		Room	−2.7	−5.5		−5.5		mA
Logic Supply Current	I$_L$	V$_{IN}$ = 0 V, or 5 V	Room	3.1		4.5		4.5	mA
Reference Supply Current	I$_R$		Room	−1	−2		−2		mA

Notes:
a. Refer to PROCESS OPTION FLOWCHART .
b. Room = 25°C, Full = as determined by the operating temperature suffix.
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e. Guaranteed by design, not subject to production test.
f. V$_{IN}$ = input voltage to perform proper function.

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Typical Characteristics

Supply Current vs. Temperature

I_{IN} vs. V_{IN} and Temperature

$r_{DS(on)}$ vs. Temperature

Switching Time vs. V_D and Temperature (DG183)

Leakage vs. Temperature (DG183)

Switching Time vs. V_D and Temperature (DG184/185)

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DG183/184/185

Typical Characteristics (Cont'd)

$I_{D(off)}$ vs. Temperature (DG184/185)

$V+ = 10$ V, $V- = -20$ V
$V_D = -10$ V, $V_S = 10$ V

B Suffix

A Suffix

I_D (nA) vs Temperature (°C)

Capacitance vs. V_D or V_S (DG183)

f = 1 MHz

$C_{S(off)}$
$C_{D(on)}$
$C_{D(off)}$

$C_{S, D}$ (pF) vs V_D or V_S – Drain or Source Voltage (V)

Capacitance vs. V_D or V_S (DG184/185)

$V_{INL} = 0.8$ V
$V_{INH} = 2$ V
f = 1 MHz

$C_{D(on)}$
$C_{S(off)}$
$C_{D(off)}$

Capacitance is measured from test terminal to common.

$C_{S, D}$ (pF) vs V_D or V_S – Drain or Source Voltage (V)

Off Isolation vs. Frequency

DG184/185
DG183

$V+ = 15$ V, $V- = -15$ V
$V_R = 0$, $V_L = 5$ V
$R_L = 75$ Ω
$V_{IN} \geq 220$ mV_{RMS}

ISO (dB) vs f – Frequency (Hz)

Test Circuits

Feedthrough due to charge injection may result in spikes at the leading and trailing edge of the output waveform.

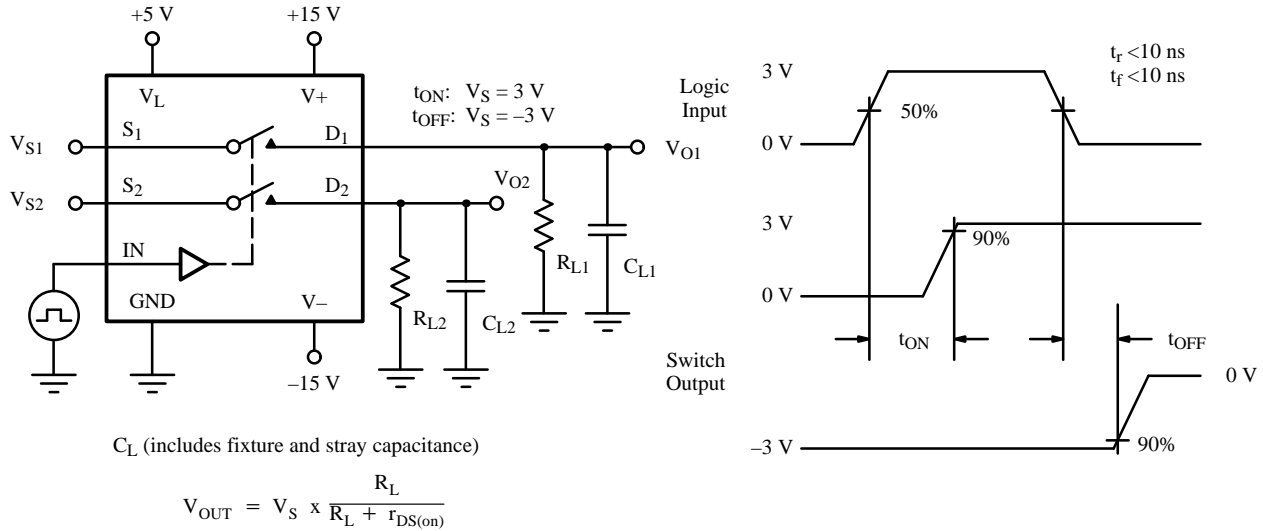$$V_{OUT} = V_S \times \frac{R_L}{R_L + r_{DS(on)}}$$

C_L (includes fixture and stray capacitance)

Figure 2. Switching Time

Application Hints[a]

Switch	V+ Positive Supply Voltage (V)	V− Negative Supply Voltage (V)	V_L Logic Supply Voltage (V)	V_R Reference Supply Voltage (V)	V_IN Logic Input Voltage $V_{INH(min)}$/$V_{INL(max)}$ (V)	V_S Analog Voltage Range (V)
DG183 DG184	15[b]	−15	5	GND	2.0/0.8	−7.5 to 15
	10	−20	5	GND	2.0/0.8	−12.5 to 10
	12	−12	5	GND	2.0/0.8	−4.5 to 12
DG185	15[b]	−15	5	GND	2.0/0.8	−10 to 15
	10	−20	5	GND	2.0/0.8	−15 to 10
	12	−12	5	GND	2.0/0.8	−7 to 12

Notes:
a. Application Hints are for DESIGN AID ONLY, not guaranteed and not subject to production testing.
b. Electrical Parameter Chart based on V+ = 15 V, V_L = 5 V, V_R = GND.